JA600020000P30; 6 – 20 GHz 1W AMPLIFIER

- **Solid-state Class AB design**
- **Ultrawide-band Operation**
- **GaN Transistor**
- **High reliability and ruggedness**

ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

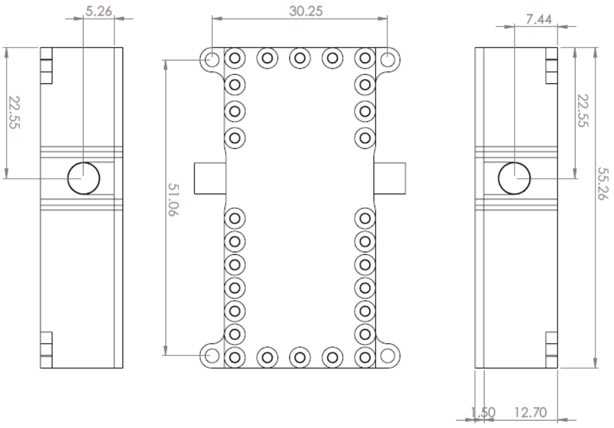
Frequency:	6000-20000 MHz
Output Power:	1W typ.
RF input for Rated Output:	15 dBm typ.
Nominal Gain (@ SS input):	14 ± 2 dB typ.
Input VSWR:	2:1 max.
DC Supply Voltage:	28 V
Enable Speed:	3 µs max.
Operating Case Temp.:	-40 ºC to 85 ºC External Heatsink Required
Storage Temperature:	-40 ºC to 85 ºC
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
4-PIN OUT:	1) GND 2) 10V 3) VGG1: -0.55V 4) VGG2: 3.5V

MECHANICAL SPECIFICATIONS

Size (mm) :	55.6 x 39 x 14.3 mm
Weight :	45 gr.
Plating :	Yellow Chromate



GENERAL DESCRIPTION

RFTR’s JA600020000P30 is a reliable ultrawide-band 1W amplifier operating between 6000-20000 MHz and suitable for CW or Pulsed waveforms. This amplifier can be used in different applications such as radars, datalinks, mobile jamming. JA600020000P30 survives under ∞:1 load VSWR condition. The PA can be enabled/disabled as fast as 3 µs that makes it suitable for power saving during pulsed applications.

JA600020000P30 is designed with the components that do not require any export license.